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<input type="checkbox"/>	L16	L15 and (HSG or hemispherical)	9
<input type="checkbox"/>	L15	L14 and capacitor	55
<input type="checkbox"/>	L14	(tungsten adj nitride) same (aluminum adj oxide)	211
<input type="checkbox"/>	L13	L12 and nitride and (aluminum or AlO3)	204
<input type="checkbox"/>	L12	(L11 or L9 or L8 or L7)	1175
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<input type="checkbox"/>	L10	L8 and (HSG or hemispherical).clm.	370
<input type="checkbox"/>	L9	L8 and (HSG or hemispherical).clm.	173
<input type="checkbox"/>	L8	438/398.ccls.	801
<input type="checkbox"/>	L7	(L5 or L6) and (HSG or (hemispherical adj grain\$2))	898
<input type="checkbox"/>	L6	257/532,534.ccls.	2129
<input type="checkbox"/>	L5	438/396-399.ccls.	5318
<input type="checkbox"/>	L4	((HSG with (etch\$5 or HF)) same (native adj oxide)) and (aluminum adj oxide) and nitride	6
<input type="checkbox"/>	L3	L2 and HF	44
<input type="checkbox"/>	L2	(open\$3 with grains) and HSG	133
<input type="checkbox"/>	L1	(HF with grains) and capacitor and HSG	22

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IEEE JNL IEEE Journal or Magazine

IEE JNL IEE Journal or Magazine

IEEE CNF IEEE Conference Proceeding

IEE CNF IEE Conference Proceeding

IEEE STD IEEE Standard

Select Article Information



1. Fabrication and performance of selective HSG storage cells for 256 Mb and 1 Gb DRAM appl
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**6. A cost effective embedded DRAM integration for high density memory and high performanc
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